



### STP42N65M5 Information



For Reference Only

Part Number STP42N65M5

Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 650V 33A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









## **STP42N65M5 Specifications**

Manufacturer Part Number         STP42N65M5           Manufacturer         STMicroelectronics           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         MDmesh? V           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         650V           Current - Continuous Drain (Id) @ 25°C         33A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         100nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         4650pF @ 100V           Vgs (Max)         ±25V           FET Feature         -           Power Dissipation (Max)         190W (Tc)           Rds On (Max) @ Id, Vgs         79 mOhm @ 16.5A, 10V           Operating Temperature         150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220-3           Package / Case         TO-220-3           Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series MDmesh? V FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 33A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 100nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 4650pF @ 100V Vgs (Max) FET Feature Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 79 mOhm @ 16.5A, 10V Operating Temperature Mounting Type Supplier Device Package Package / Case TO-220-3 Package / Case	Manufacturer Part Number	STP42N65M5
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C33A (Te)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4650pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs79 mOhm @ 16.5A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3	Series	MDmesh? V
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Operating Temperature 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220-3  Package / Case TO-220-3	Power Dissipation (Max)	190W (Tc)
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Supplier Device Package TO-220-3 Package / Case TO-220-3	Operating Temperature	150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3
		Report errors?

#### STP42N65M5 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### STP42N65M5 Payment Methods



















# STP42N65M5 Shipping Methods













If you have any question about STP42N65M5, please do not hesitate to contact us!

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